

15EC63

# Sixth Semester B.E. Degree Examination, Dec.2019/Jan.2020 **VLSI Design**

Time: 3 hrs.

Max. Marks: 80

Note: Answer any FIVE full questions, choosing ONE full question from each module.

Module-1

- a. Explain the step-by-step CMOS P-Well fabrication process. (08 Marks)
  - b. With the mathematical equations, explain velocity saturation and mobility degradation effect due to increase in saturation current. (08 Marks)

OR

- a. With the transfer characteristic of skewed inverter, explain the beta ratio effects.
   b. Compare CMOS and bipolar technologies.
  - c. Compare CMOS and bipolar technologies.
     c. Consider the nMOS transistor in a 180 nm process with a nominal threshold of 0.4V and doping level of 8 × 10<sup>17</sup> cm<sup>-3</sup>. The body is tied to ground with a substrate contact. How much does the threshold change at room temperature if the source is at 1.1V instead of '0'?

(04 Marks)

Module-2

- 3 a. Discuss the λ-based design rules (i) Butting contact (ii) Transistors (nMOS, pMOS and CMOS)
   (08 Marks)
  - b. Derive the expression of delay interms of  $\tau$  for CMOS inverter pair.

(08 Marks)

OR

a. Draw the layout for  $\overline{Y} = A + BC$  using CMOS.

(08 Marks)

b. Find the C<sub>in</sub> for the layout shown in Fig.Q4(b).

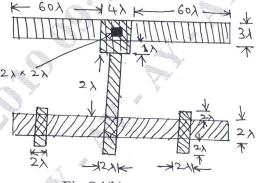


Fig.Q4(b) (08 Marks)

Module-3

- 5 a. Define scaling. Explain the scaling factors for device parameters.
  - b. What is Manchester Carry Chain? Explain it.

(08 Marks) (08 Marks)

OR

- 6 a. What are the problems associated with VLSI design and how to reduce by using standard practice? (06 Marks)
  - b. Draw the  $4 \times 4$  cross bar switch using MOS switches and explain it.

(06 Marks)

c. Calculate the Regularity for  $4 \times 4$  bit and  $8 \times 8$  bit shifter.

(04 Marks)

(08 Marks)

### Module-4

7 a. Construct a stick diagram for an nMOS parity generator as shown in Fig.Q7(a). The required response is such that z = 1 if there is an even number (including zero) of 1s on the input and z = 0 if there is an odd number.

Fig.Q7(a) (08 Marks)

b. Draw the block diagram of Generic structure of an FPGA fabric and explain it.

#### OR

8 a. Construct a stick diagram for an multiplexer shown in Fig.Q8(a) using CMOS.

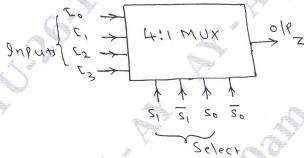


Fig.Q8(a) (08 Marks)

b. Explain the goals and techniques of FPGA based system design. (08 Marks)

## Module-5

- 9 a. What are the requirements for system timing considerations? (06 Marks)
  b. Explain the operation of a three transistor dynamic RAM cell. (06 Marks)
  - c. Write a note on stuck at faults. (04 Marks)

#### OR

a. With the help of block diagram, explain the process of logic verification.
b. Explain the operation of CMOS pseudo-static memory cell.
(08 Marks)
(08 Marks)

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